



### Description

The SI2308 uses advanced trench technology to provide excellent  $R_{DS(ON)}$ . This device is suitable for use as a load switch or in PWM applications.

### General Features

$V_{DS} = 60V, I_D = 2.5A$

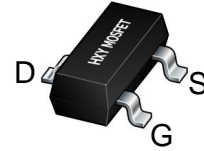
$R_{DS(ON)} < 85m\Omega @ V_{GS} = 10V$

### Application

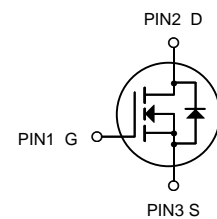
Battery protection

Load switch

Uninterruptible power supply



SOT-23



N-Channel MOSFET

### Package Marking and Ordering Information

Product ID	Pack	Marking	Qty(PCS)
SI2308	SOT-23	MS08/6003	3000

### Absolute Maximum Ratings (TA=25°C unless otherwise noted)

Symbol	Parameter	Limit	Unit
$V_{DS}$	Drain-Source Voltage	60	V
$V_{GS}$	Gate-Source Voltage	$\pm 20$	V
$I_D$	Drain Current-Continuous	2.5	A
$I_{DM}$	Drain Current-Pulsed (Note 1)	10	A
$P_D$	Maximum Power Dissipation	1.25	W
$T_J, T_{STG}$	Operating Junction and Storage Temperature Range	-55 To 150	°C
$R_{\theta JA}$	Thermal Resistance, Junction-to-Ambient (Note 2)	62.5	°C/W



**Electrical Characteristics (T<sub>A</sub>=25°C unless otherwise noted)**

Symbol	Parameter	Condition	Min	Typ	Max	Unit
<b>Static Parameters</b>						
V <sub>(BR)DSS</sub>	Drain-Source Breakdown Voltage	V <sub>GS</sub> =0V, I <sub>D</sub> =250uA	60			V
V <sub>GS(th)</sub>	Gate Threshold Voltage	V <sub>DS</sub> =V <sub>GS</sub> , I <sub>D</sub> =250uA	1.0		2	V
I <sub>GSS</sub>	Gate Leakage Current	V <sub>DS</sub> =0V, V <sub>GS</sub> =±12V			±100	nA
I <sub>DSS</sub>	Zero Gate Voltage Drain Current	V <sub>DS</sub> =44V, V <sub>GS</sub> =0			1	uA
		V <sub>DS</sub> =44V, V <sub>GS</sub> =0 T <sub>J</sub> =85°C			5	
I <sub>D(ON)</sub>	On=State Drain Current	V <sub>DS</sub> ≥5V, V <sub>GS</sub> =4.5V	10			A
R <sub>DS(ON)</sub>	Drain-Source On-Resistance	V <sub>GS</sub> =10V, I <sub>D</sub> =1.8A		72	85	mΩ
		V <sub>GS</sub> =4.5V, I <sub>D</sub> =1.5A		85	103	
G <sub>fs</sub>	Forward Transconductance	V <sub>DS</sub> =5V, I <sub>D</sub> =2.1A		10		S
<b>Source-Drain Diode</b>						
V <sub>SD</sub>	Diode Forward Voltage	I <sub>S</sub> =1.0A, V <sub>GS</sub> =0V		0.8	1.0	V
<b>Dynamic Parameters</b>						
Q <sub>g</sub>	Total Gate Charge	V <sub>DS</sub> =27V V <sub>GS</sub> =4.5V I <sub>D</sub> =2.1A		2.1	3.9	nC
Q <sub>gs</sub>	Gate-Source Charge			0.6		
Q <sub>gd</sub>	Gate-Drain Charge			0.8		
C <sub>iss</sub>	Input Capacitance	V <sub>DS</sub> =25V V <sub>GS</sub> =0V f=1MHz		295		pF
C <sub>oss</sub>	Output Capacitance			40		
C <sub>rss</sub>	Reverse Transfer Capacitance			15		
T <sub>d(on)</sub>	Turn-On Time	V <sub>DS</sub> =27V R <sub>L</sub> =10Ω I <sub>D</sub> =1A		3.6		nS
T <sub>r</sub>				3.5		
T <sub>d(off)</sub>	Turn-Off Time		V <sub>GEN</sub> =4.5V R <sub>G</sub> =6Ω		32	
T <sub>f</sub>				3		

**Note: 1. Pulse test: pulse width≤300uS, duty cycle≤2%**

**2.Static parameters are based on package level with recommended wire bonding**



### Typical Characteristics

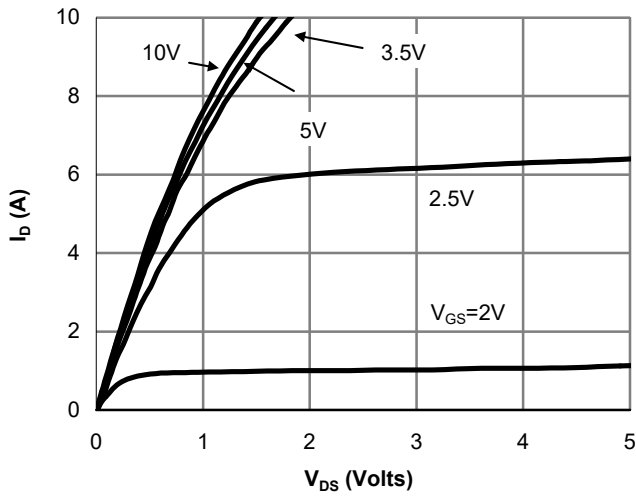


Fig 1: On-Region characteristics

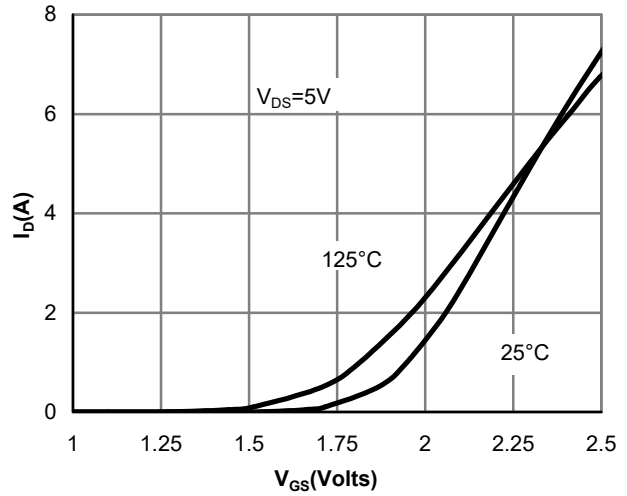


Figure 2: Transfer Characteristics

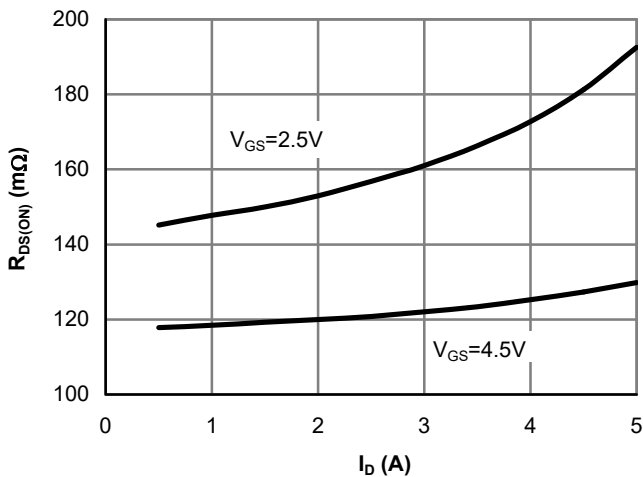


Figure 3: On-Resistance vs. Drain Current and Gate Voltage

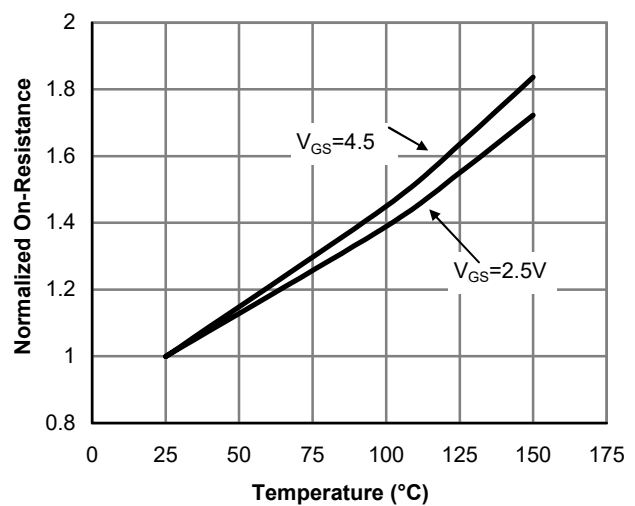


Figure 4: On-Resistance vs. Junction Temperature

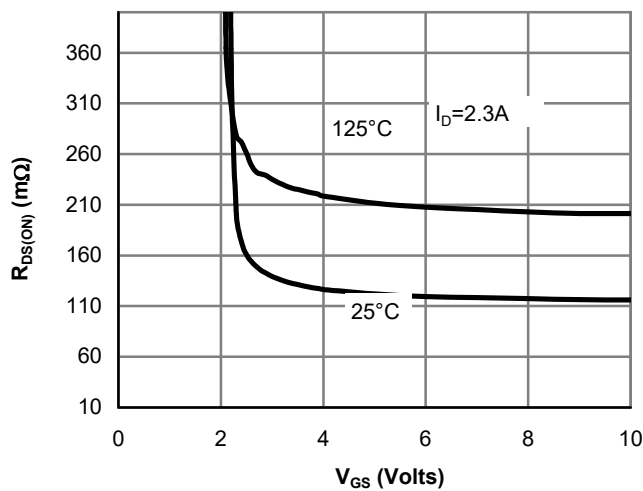


Figure 5: On-Resistance vs. Gate-Source Voltage

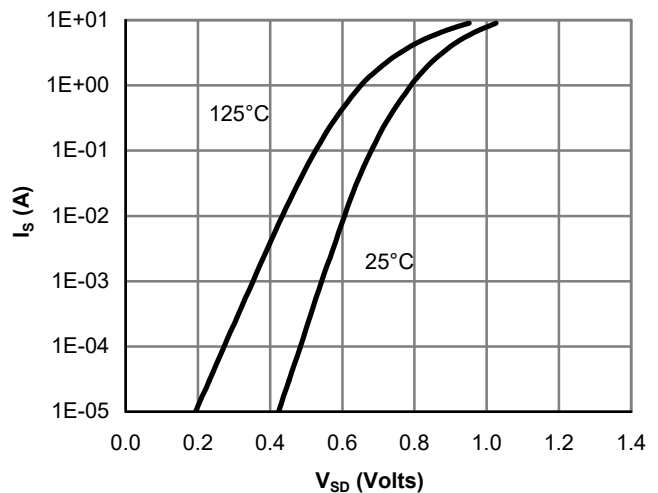


Figure 6: Body-Diode Characteristics

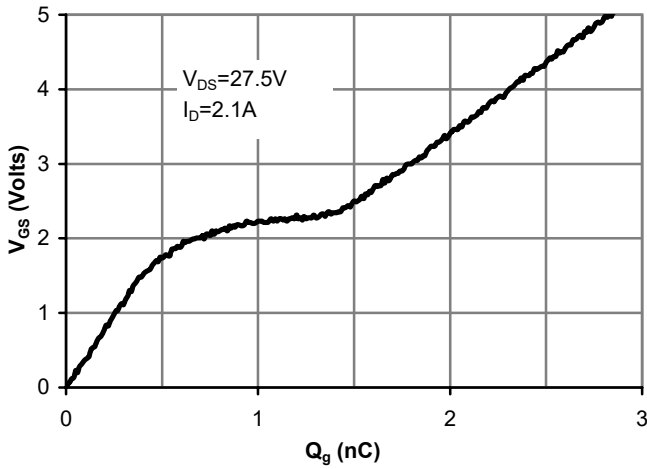


Figure 7: Gate-Charge Characteristics

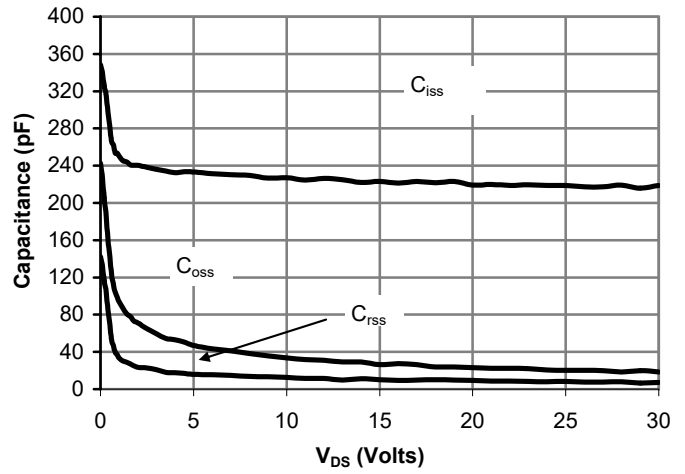


Figure 8: Capacitance Characteristics

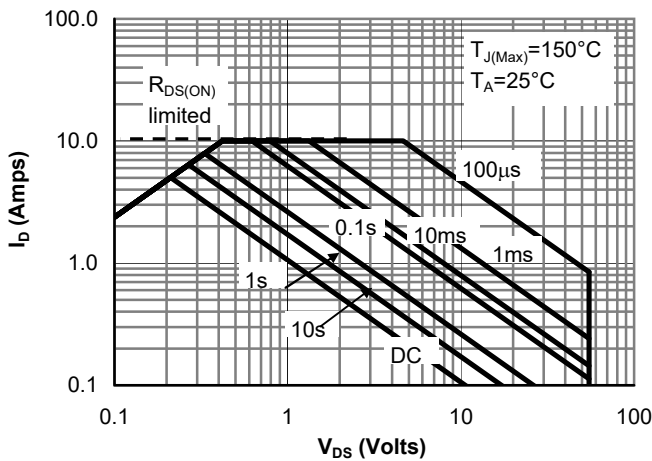


Figure 9: Maximum Forward Biased Safe Operating Area (Note E)

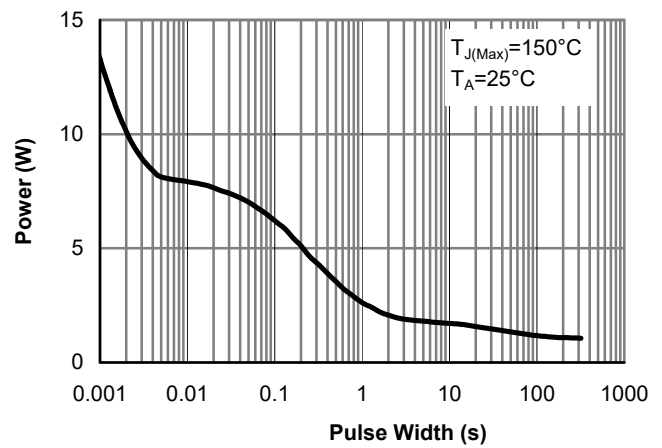


Figure 10: Single Pulse Power Rating Junction-to-Ambient (Note E)

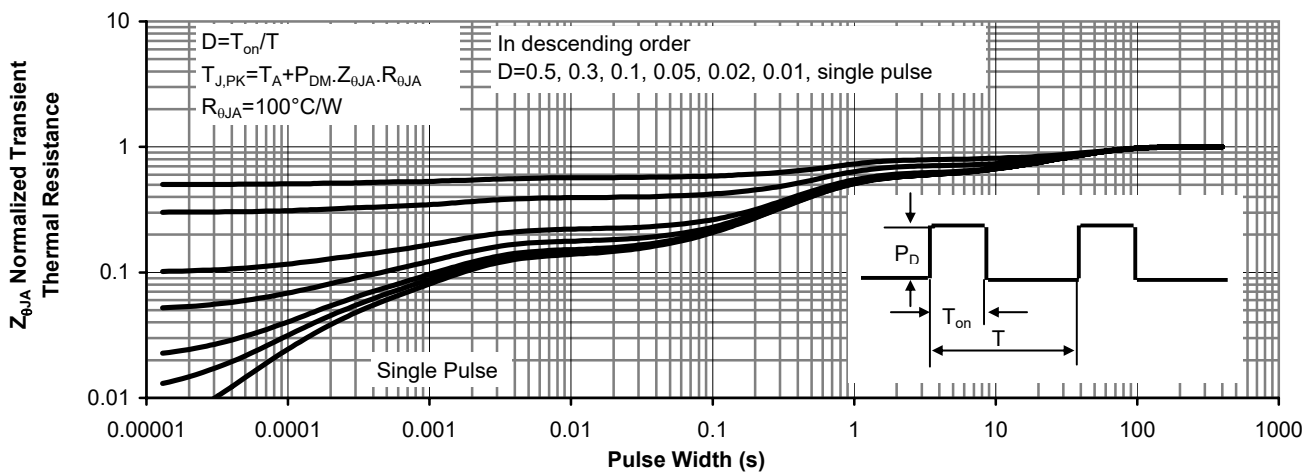
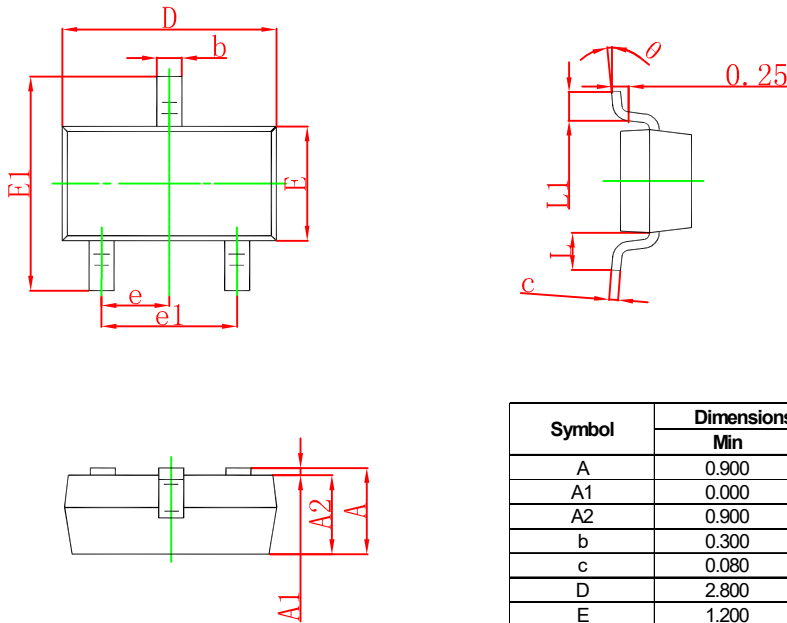


Figure 11: Normalized Maximum Transient Thermal Impedance

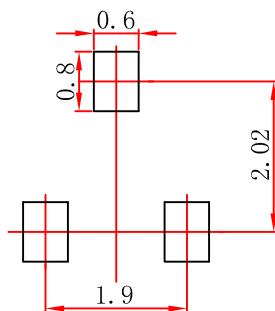


### SOT-23 Package Outline Dimensions



Symbol	Dimensions In Millimeters		Dimensions In Inches	
	Min	Max	Min	Max
A	0.900	1.150	0.035	0.045
A1	0.000	0.100	0.000	0.004
A2	0.900	1.050	0.035	0.041
b	0.300	0.500	0.012	0.020
c	0.080	0.150	0.003	0.006
D	2.800	3.000	0.110	0.118
E	1.200	1.400	0.047	0.055
E1	2.250	2.550	0.089	0.100
e	0.950 TYP		0.037 TYP	
e1	1.800	2.000	0.071	0.079
L	0.550 REF		0.022 REF	
L1	0.300	0.500	0.012	0.020
θ	0°	8°	0°	8°

### SOT-23 Suggested Pad Layout



**Note:**

1. Controlling dimension: in millimeters.
2. General tolerance:  $\pm 0.05\text{mm}$ .
3. The pad layout is for reference purposes only.



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